



DMP2047UCB4

Product Summary (Typ. @ V_{GS} = -4.5V, T_A = +25°C)

| BVDSS | RDS(ON) | Qg | Qgd | ID |
|-------|---------|-------|-------|-------|
| -20V | 40mΩ | 2.3nC | 0.4nC | -4.1A |

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Battery Management
- Load Switch
- Battery Protection

Features

• LD-MOS Technology with the Lowest Figure of Merit: $R_{DS(ON)} = 40m\Omega$ to Minimize On-State Losses $Q_g = 2.3nC$ for Ultra-Fast Switching

P-CHANNEL ENHANCEMENT MODE MOSFET

- V_{GS(th)} = -0.8V typ. for a Low Turn-On Potential
- CSP with Footprint 1.0mm × 1.0mm
- Height = 0.62mm for Low Profile
- ESD = 3kV HBM Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

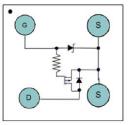
 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Case: U-WLB1010-4
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal: Finish SnAgCu. Solderable per MIL-STD-202 Method
 208
- Weight: 0.0018 grams (Approximate)

U-WLB1010-4





Top View Equivalent Circuit

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|-------------|-------------------|
| DMP2047UCB4-7 | U-WLB1010-4 | 3,000/Tape & Reel |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

U-WLB1010-4



DW = Product Type Marking Code $\begin{array}{l} YM = \text{Date Code Marking } \\ YM = \text{Date Code Marking} \\ Y = \text{Year (ex: H = 2020)} \\ M = \text{Month (ex: 9 = \text{September)}} \end{array}$ c = Assembly Code

Date Code Key

| Year | 2012 | | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 |
|-------|------|-----|------|------|------|------|------|------|------|------|------|------|
| Code | Z | | Н | | J | К | L | М | Ν | 0 | Р | R |
| Month | Jan | Feb | Mar | Apr | Мау | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| | | | | | | | | | | | | |

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|-----------------|--|------------------|--------------|---|
| Drain-Source Voltage | VDSS | -20 | V | | |
| Gate-Source Voltage | | | V _{GSS} | -6 | V |
| Continuous Drain Current (Note 5) V _{GS} = -4.5V | Steady State | T _A = +25°C T _A = +70°C | D | -4.1 -3.2 | А |
| Continuous Drain Current (Note 5) V_{GS} = -2.5V | Steady State | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | ID | -3.6 -2.8 | A |
| Pulsed Drain Current (Note 6) | Ідм | -16 | А | | |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|------------------|-------------|------|
| Power Dissipation (Note 7) | PD | 1.0 | W |
| Thermal Resistance, Junction to Ambient @ $T_A = +25$ °C (Note 7) | R _{0JA} | 127 | °C/W |
| Thermal Resistance, Junction to Case @ $T_C = +25^{\circ}C$ (Note 7) | Rejc | 25.8 | °C/W |
| Power Dissipation (Note 5) | PD | 1.66 | W |
| Thermal Resistance, Junction to Ambient @ $T_A = +25^{\circ}C$ (Note 5) | R _{0JA} | 77 | °C/W |
| Operating and Storage Temperature Range | TJ, TSTG | -55 to +150 | °C |

Notes: 5. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

Repetitive rating, pulse width limited by junction temperature.
 Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.



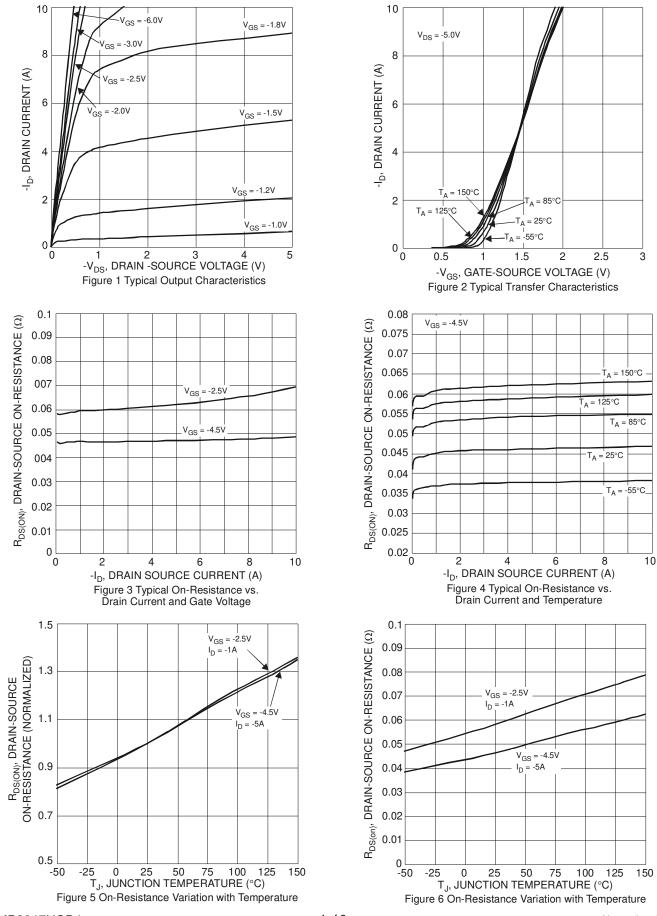
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Cumphed | Min | T.m | Max | Unit | Test Condition |
|--|-------------------|------|-------|------|-------|---|
| | Symbol | WIIN | Тур | Max | Unit | Test Condition |
| OFF CHARACTERISTICS (Note 8) | | | 1 | 1 | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -20 | _ | — | V | $V_{GS} = 0V, I_D = -250 \mu A$ |
| Gate-Source Breakdown Voltage | BVGSS | -6.0 | | — | V | $V_{DS} = 0V, I_{G} = -250\mu A$ |
| Zero Gate Voltage Drain Current TJ = +25°C | IDSS | _ | — | -1 | μA | $V_{DS} = -16V, V_{GS} = 0V$ |
| Gate-Source Leakage | IGSS | — | | -100 | nA | $V_{GS}=-6V,V_{DS}=0V$ |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | VGS(TH) | -0.4 | -0.8 | -1.2 | V | $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ |
| Static Drain-Source On-Resistance | Descer | — | 40 | 47 | mΩ | VGS = -4.5V, ID =-1A |
| | RDS(ON) | | 53 | 60 | 11122 | $V_{GS} = -2.5V, I_D = -1A$ |
| Forward Transfer Admittance | Y _{fs} | _ | 3.7 | — | S | VDS = -10V, ID = -1A |
| Diode Forward Voltage | Vsd | | -0.7 | -1.0 | V | Vgs = 0V, Is = -1A |
| Reverse Recovery Charge | QRR | _ | 3.07 | _ | nC | V _{DD} = -10V, I _F = -1A, |
| Reverse Recovery Time | trr | _ | 13.14 | _ | ns | di/dt =100A/µs |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | · |
| Input Capacitance | Ciss | | 218 | _ | | $V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz |
| Output Capacitance | Coss | | 116 | _ | pF | |
| Reverse Transfer Capacitance | Crss | | 11 | _ | | 1 = 1.0MHz |
| Total Gate Charge | Qg | _ | 2.3 | _ | | |
| Gate-Source Charge | Qgs | _ | 0.2 | — | nC | VGS = -4.5V, VDS = -10V, |
| Gate-Drain Charge | Q _{gd} | _ | 0.4 | — | nC | I _D = -1A |
| Gate Charge at Vth | Qg(th) | _ | 0.2 | — | | |
| Turn-On Delay Time | tD(ON) | _ | 7.9 | — | | |
| Turn-On Rise Time | t _R | _ | 10.7 | — | 1 | $V_{DS} = -10V, V_{GS} = -2.5V,$ |
| Turn-Off Delay Time | tD(OFF) | _ | 48 | _ | ns | $R_G = 20\Omega, I_D = -1A$ |
| Turn-Off Fall Time | tF | | 38 | _ | | |

8. Short duration pulse test used to minimize self-heating effect.9. Guaranteed by design. Not subject to production testing. Notes:



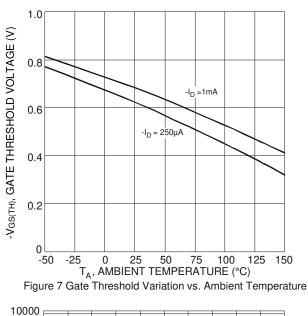
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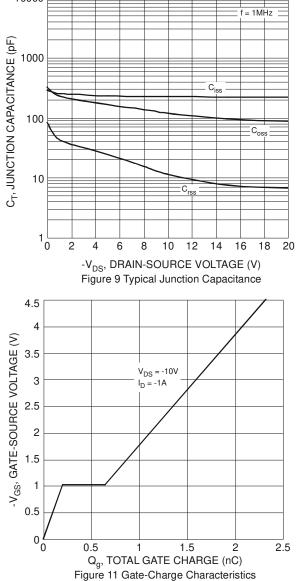


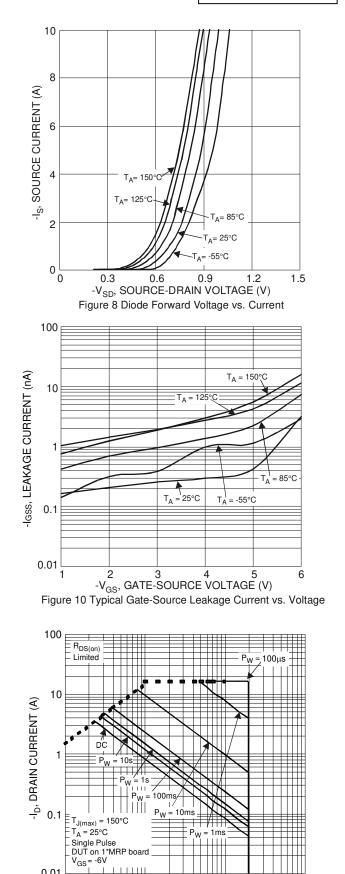
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0.01 0.1

100

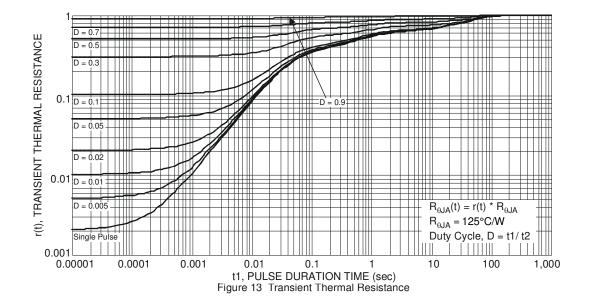
1m

10

-V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12 SOA, Safe Operation Area

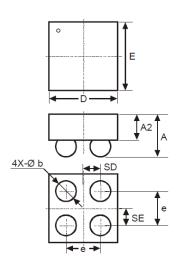






Package Outline Dimensions

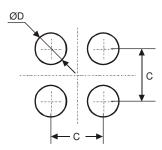
Please see http://www.diodes.com/package-outlines.html for the latest version.



| U-WLB1010-4 | | | | | | | |
|-------------|--------|-----------|------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| D | 0.95 | 1.05 | 1.00 | | | | |
| ш | 0.95 | 1.05 | 1.00 | | | | |
| Α | - | 0.62 | - | | | | |
| A2 | - | - | 0.38 | | | | |
| b | 0.25 | 0.35 | 0.30 | | | | |
| e | - | - | 0.50 | | | | |
| SD | - | - | 0.25 | | | | |
| SE | - | - | 0.25 | | | | |
| All | Dimens | ions in I | nm | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



U-WLB1010-4

| Dimensions | Value (in mm) |
|------------|---------------|
| С | 0.50 |
| D | 0.25 |

U-WLB1010-4



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